

## Thyristor – Thyristor Module

### Features

- Improved glass passivation for high reliability
- Exceptional stability at high temperatures
- High di/dt and dv/dt capabilities
- Low thermal resistance

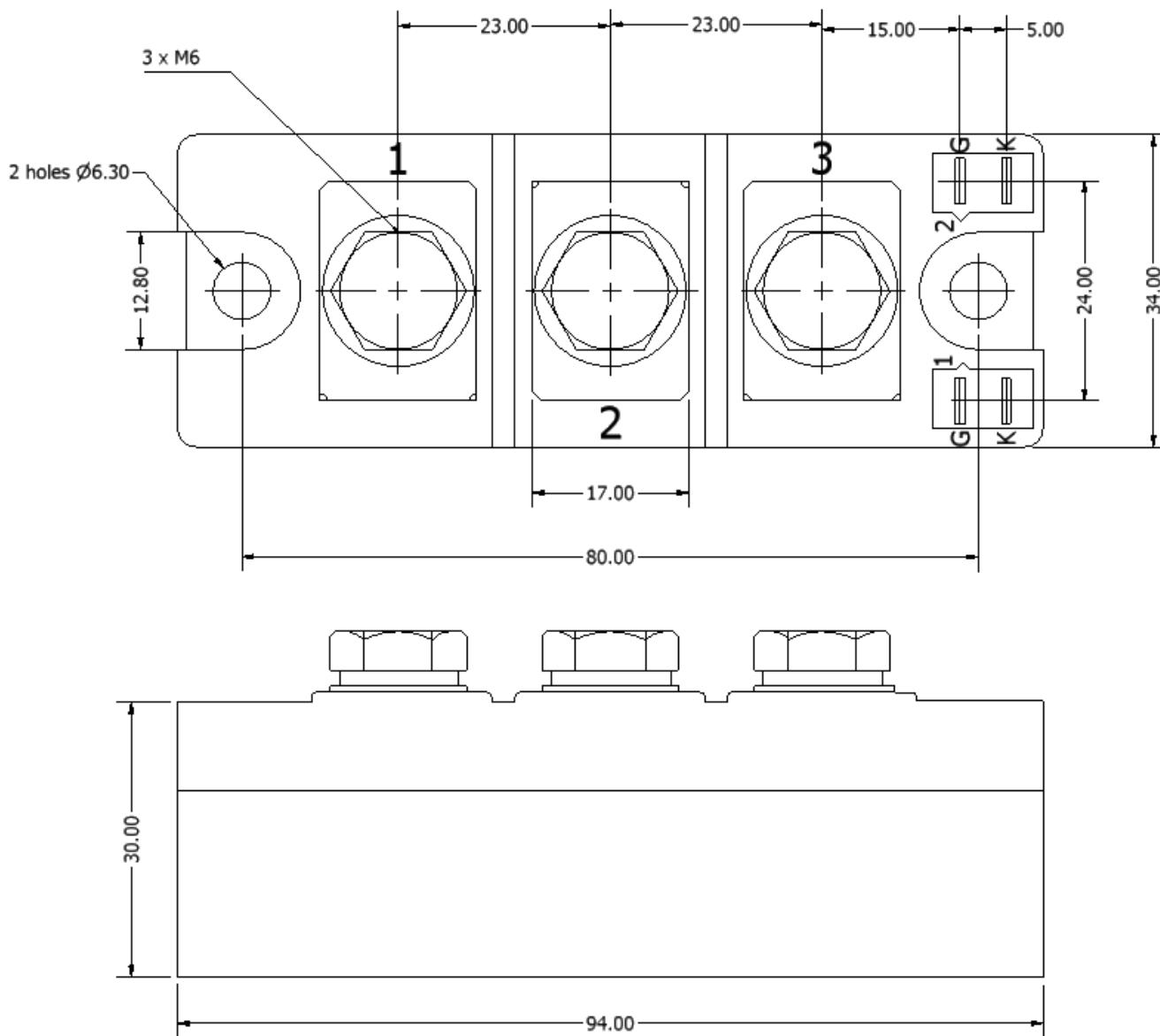
Maximum Ratings ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)			
Parameter	Symbol	Values	Units
Maximum average forward current @ $T_J = 85^{\circ}\text{C}$	$I_{F(AV)}$	160	A
Maximum average RMS forward current	$I_{F(\text{RMS})}$	350	A
Maximum non-repetitive surge current @ $t = 10\text{ms}$	$I_{FSM}$	5100	A
Maximum $I^2t$ for fusing @ $t = 10\text{ms}$	$I^2t$	120	kA <sup>2</sup> s



**M3 PACKAGE**

Thermal & Mechanical Specifications ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)			
Parameter	Symbol	Values	Units
Operating junction temperature range	$T_J$	-65 to +125	$^{\circ}\text{C}$
Thermal resistance, junction to case	$R_{th(JC)}$	0.16	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)			
Parameter	Symbol	Values	Units
Maximum average on-state current	$I_{T(\text{max})}$	160	A
Maximum repetitive peak reverse voltage range	$V_{RRM}$	200 to 1600	V
Forward voltage drop	$V_{FM}$	1.5	V
Gate current required to trigger	$I_{GT}$	150	mA
Gate voltage required to trigger	$V_{GT}$	2.5	V
Holding current range	$I_H$	200	mA
Maximum latching current	$I_L$	500	mA
Critical rate of rise of off-state voltage	$dv/dt$	1000	V/ $\mu$ s
RMS isolated voltage	$V_{ISO}$	3500	V



ALL DIMENSIONS IN MM

**Diode Configuration**